## An ELNES study of LiAlO<sub>2</sub>

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 $(100)\gamma$ -LiAlO<sub>2</sub> is considered to be a promising substrate which allows for growth of both c- and m-plane oriented GaN layers [1]. In contrast to conventional substrates like SiC the advantage of  $(100)\gamma$ -LiAlO<sub>2</sub> is the very small lattice mismatch of about 1.4%. Also, it allows the growing of non-polar m-plane GaN which shows absence of internal electrostatic fields along the growing direction. This makes it possible to generate new efficient white light-emitting diodes (LEDs) [2]. At certain growth conditions the LiAlO<sub>2</sub>-single crystals contain a core of inclusions. Also at the GaN/LiAlO<sub>2</sub> interface there are inclusions which are partly surrounded by cavities in the LiAlO<sub>2</sub>-matrix. These inclusions at the interface are suspected to be the cause of a spontaneous separation of thick GaN layers. This effect may be used in the future to generate GaN layers for homoepitaxy which would allow to produce almost defect free GaN wafers.

Preliminary TEM analysis using electron diffraction showed that the inclusions mentioned above consist of  $LiAl_5O_8$  [3]. But also the formation of  $Al_2O_3$  can occur. Simulations of Oxygen K-edge ELNES spectra were carried out using the full potential linear augmented plane wave code WIEN97. TEM analysis comprising STEM and EELS was carried out on a 200 kV JEOL JEM2200FS microscope at Humboldt-University Berlin. In Figure 1 the simulated and experimental spectra are compared. Considering the known limitations of the simulation program, the very good agreement of simulation and experimental spectra is remarkable.

The investigations showed that the inclusions in  $\gamma$ -LiAlO2 consist of LiAl<sub>5</sub>O<sub>8</sub>. It was also found that the specimen is damaged due to electron beam irradiation. Comparison of ELNES simulations and experimental spectra did not only show the already known transformation of LiAlO<sub>2</sub> into LiAl<sub>5</sub>O<sub>8</sub> [4] but also an unexpected transition to Al<sub>2</sub>O<sub>3</sub> which is shown in Figure 2. At the beginning the two peaks of LiAlO<sub>2</sub> can be clearly identified, while the intensity of the first peak is decreasing until the peak is transformed to the shoulder in the rising edge of Al<sub>2</sub>O<sub>3</sub>. These changes can be attributed to the following reactions:

5 LiAlO<sub>2</sub>  $\rightarrow$  2 Li<sub>2</sub>O  $\uparrow$  + LiAl<sub>5</sub>O<sub>8</sub>

 $2 \text{ LiAl}_5\text{O}_8 \rightarrow \text{Li}_2\text{O} \uparrow + 5 \text{ Al}_2\text{O}_3.$ 

The spectra contain an additional peak at 531 eV which is marked with an arrow in Figure 2. This peak is observed as long as the transformation from LiAlO<sub>2</sub> to Al<sub>2</sub>O<sub>3</sub> takes place. This suggests that it can be associated with the loss of Li<sub>2</sub>O. The peak can be attributed to a  $\pi^*$ -resonance which occurs when an electron is excited from a  $\sigma$ -molecular orbital to a  $\pi^*$ -orbital [5]. Li<sub>2</sub>O has a similar structure as H<sub>2</sub>O which means that there are only  $\sigma$ -bondings and no  $\pi^*$ -resonance can occur. Thus, the peak at 531 eV can be attributed to molecular oxygen. We conclude that the electron beam sets free O<sub>2</sub> due to heating of the sample. This causes a change in the chemical composition of the sample so that it becomes more Al-rich.

Further investigation of the  $LiAlO_2$  transformation will allow an adaption of the production parameters for fabrication of defect-free  $LiAlO_2$ .

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**Figure 1.** Comparison of simulated and experimental ELNES spectra of oxygen K-edge. From top to bottom  $LiAlO_2$ ,  $LiAl_5O_8$  and  $Al_2O_3$ .



**Figure 2.** Spectra acquired at intervals of five seconds. The transformation of LiAlO<sub>2</sub> to  $Al_2O_3$  is clearly visible. The  $\pi^*$ -resonance peak of molecular oxygen at 531 eV is marked with an arrow.